

IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

Applicant(s) : Gou-Chung Chi, Iinn-Kong Sheu, Meng-Che Chen and Min-Lum
Date : Lee
Serial No. :
Group Art Unit:
Filed :
For : ULTRAVIOLET DETECTOR AND MANUFACTURE METHOD THEREOF

Honorable Commissioner of Patents
and Trademarks
Washington, D.C. 20231

INFORMATION DISCLOSURE STATEMENT

Sir:

Attached is a completed Form PTO-1449 and copies of the pertinent parts of the references cited thereon. Comments on any non-English-language references (if any) pursuant to Rule are submitted herewith.

Respectfully submitted

Applicants(s): G.C. Chi Iinn Kong Sheu Meng-Che Chen
Min-Lum Lee _____

Encl: PTO-1449 & References

FORM PTO-1449 (Substitute)

LIST OF PRIOR ART CITED BY APPLICANT
(Use several sheets if necessary)

ATTY. DOCKET NO.

03176-UPS

SERIAL NO.

APPLICANT

Gou-Chung Chi et al.

FILING DATE

GROUP

U.S. PATENT DOCUMENTS

*EXAMINER INITIAL		DOCUMENT NUMBER	DATE	NAME	CLASS	SUBCLASS	FILING DATE IF APPROPRIATE
	AA						
	AB						
	AC						
	AD						
	AE						
	AF						
	AG						
	AH						
	AI						
	AJ						
	AK						

FOREIGN PATENT DOCUMENTS

	AL						
	AM						
	AN						
	AO						
	AP						

OTHER PRIOR ART (Including Author, Title, Date, Pertinent Pages, Etc.)

	AR	Planar GaN n^+ - p photodetectors formed by Si implantation into p -GaN J. K. Sheu, M. L. Lee, L. S. Yeh, C. J. Kao, C. J. Tun, M. G. Chen, G. C. Chi, S. J. Chang, Y. K. Su, and C. T. Lee Department of Physics, National Central University, Chung-Li 320, Taiwan, Republic of China (Received 6 May 2002; accepted 7 October 2002)					
	AS						
	AT						

EXAMINER

DATE CONSIDERED

*EXAMINER: Initial if reference considered, whether or not citation is in conformance with MPEP 609; Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant.